

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM6N16FE

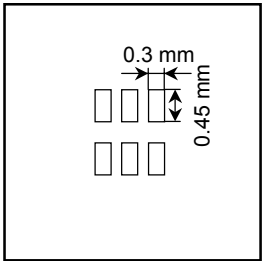
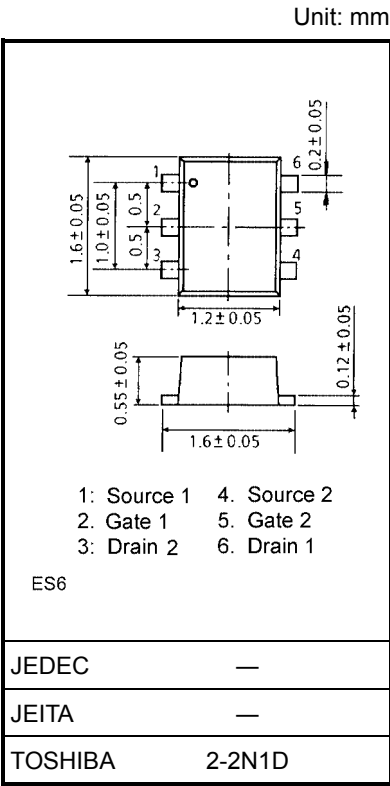
High Speed Switching Applications
Analog Switching Applications

- Suitable for high-density mounting due to compact package
- Low on resistance: $R_{on} = 3.0\ \Omega$ (max) (@ $V_{GS} = 4\text{ V}$)
 : $R_{on} = 4.0\ \Omega$ (max) (@ $V_{GS} = 2.5\text{ V}$)
 : $R_{on} = 15\ \Omega$ (max) (@ $V_{GS} = 1.5\text{ V}$)

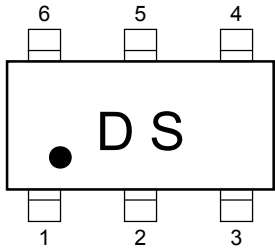
Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DS}	20	V
Gate-Source voltage		V_{GSS}	± 10	V
Drain current	DC	I_D	100	mA
	Pulse	I_{DP}	200	
Drain power dissipation (Ta = 25°C)		P_D (Note)	150	mW
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	-55~150	°C

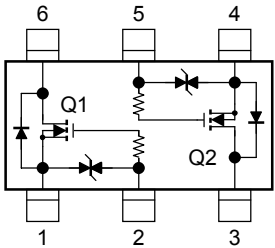
Note: Total rating, mounted on FR4 board
(25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 0.135 mm² × 6)



Marking



Equivalent Circuit



Handling Precaution

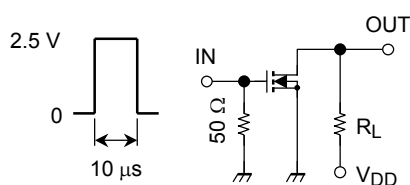
When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

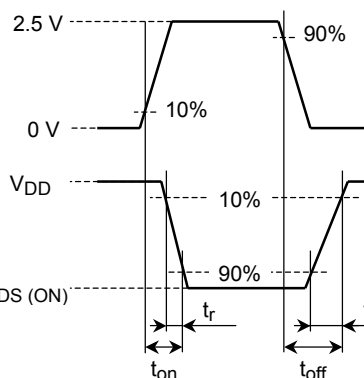
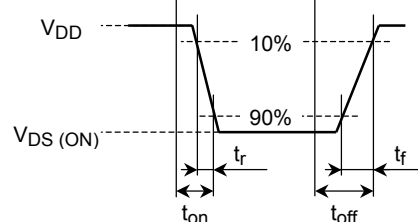
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	—	—	± 1	μA
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = 0.1 \text{ mA}, V_{GS} = 0$	20	—	—	V
Drain cut-off current	I_{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0$	—	—	1	μA
Gate threshold voltage	V_{th}	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.6	—	1.1	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$	40	—	—	mS
Drain-Source ON resistance	$R_{DS(ON)}$	$I_D = 10 \text{ mA}, V_{GS} = 4 \text{ V}$	—	1.5	3.0	Ω
		$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	—	2.2	4.0	
		$I_D = 1 \text{ mA}, V_{GS} = 1.5 \text{ V}$	—	5.2	15	
Input capacitance	C_{iss}	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	—	9.3	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	—	4.5	—	pF
Output capacitance	C_{oss}	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	—	9.8	—	pF
Switching time	Turn-on time	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0 \sim 2.5 \text{ V}$	—	70	—	ns
	Turn-off time		—	125	—	

Switching Time Test Circuit

(a) Test circuit



$V_{DD} = 3 \text{ V}$
 Duty $\leq 1\%$
 V_{IN} : $t_r, t_f < 5 \text{ ns}$
 $(Z_{out} = 50 \Omega)$
 Common Source
 $T_a = 25^\circ\text{C}$

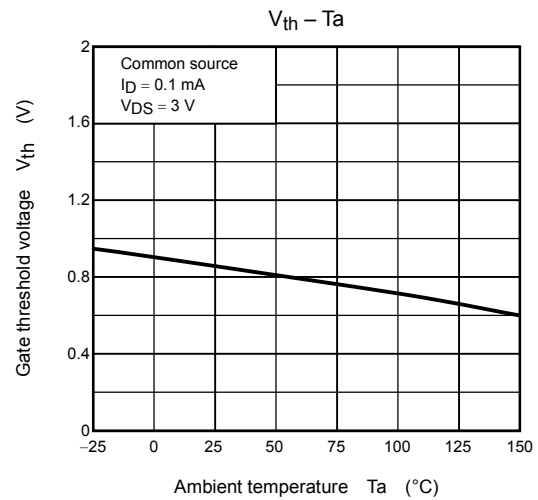
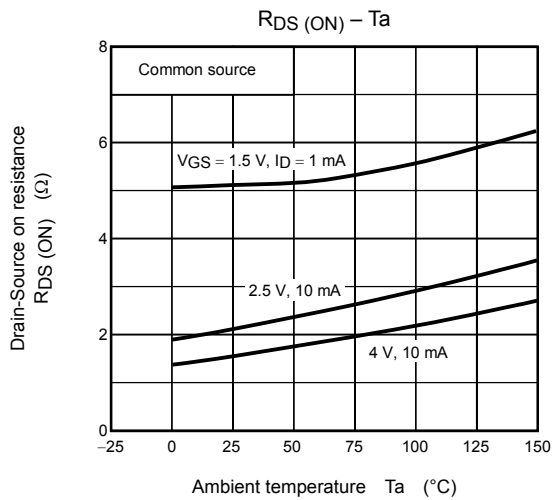
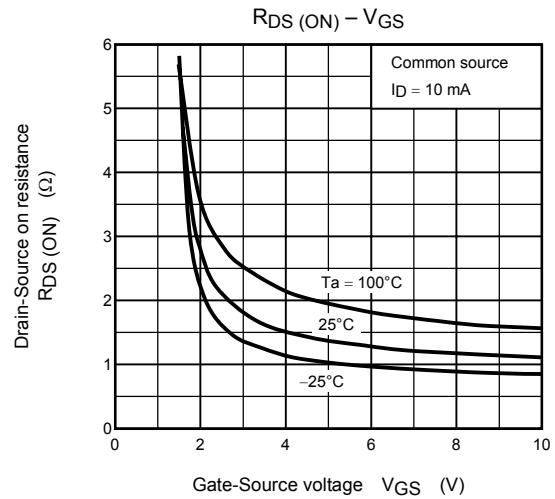
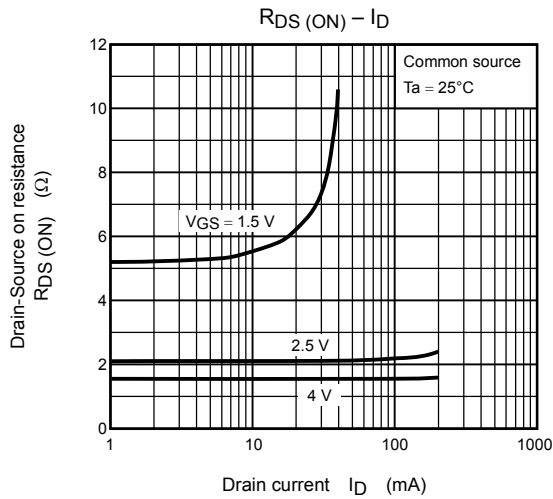
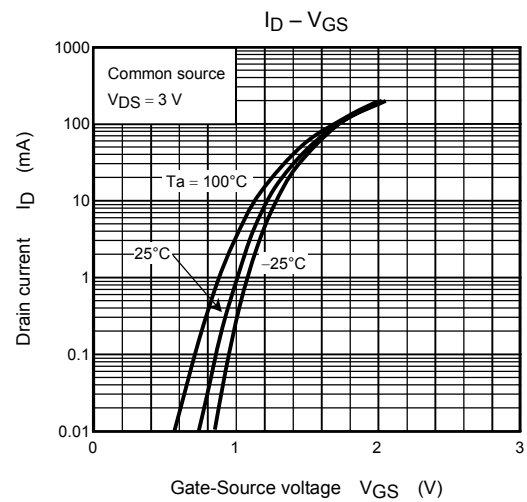
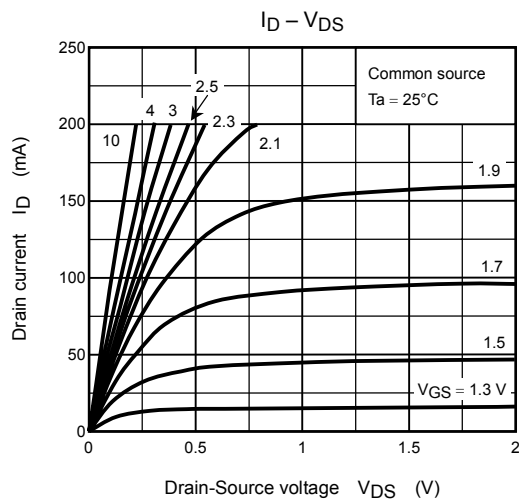
(b) V_{IN} (c) V_{OUT} 

Precaution

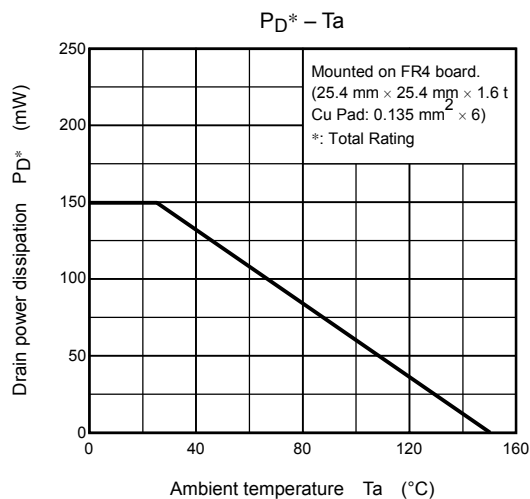
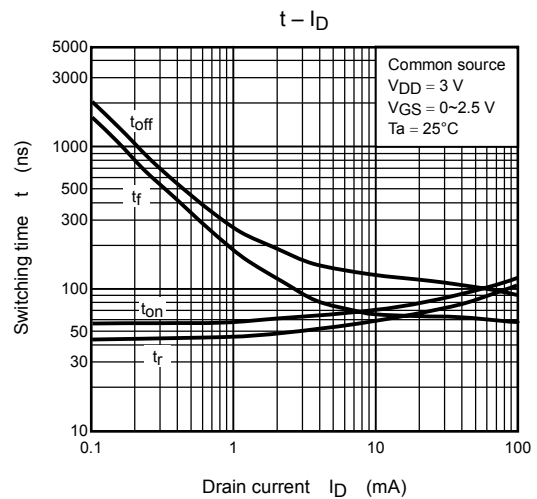
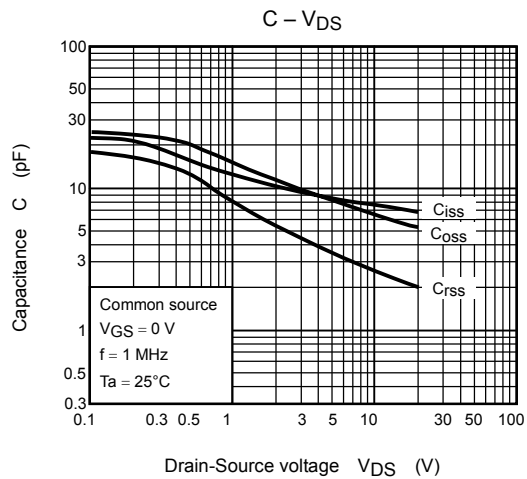
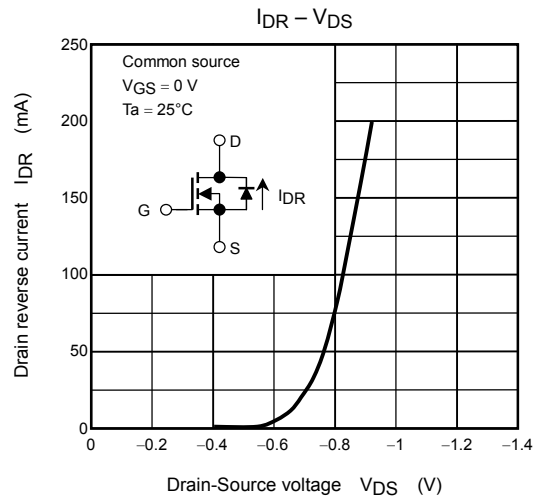
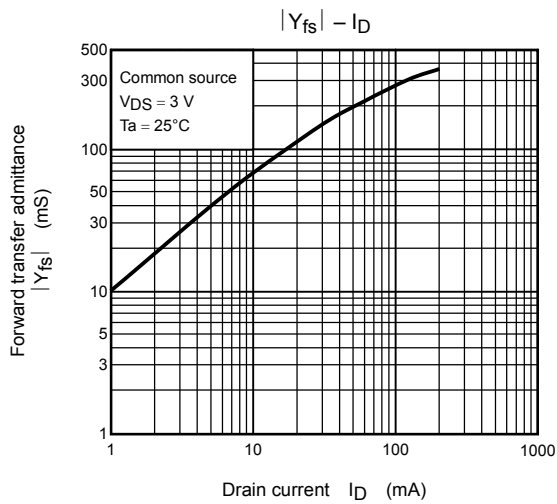
V_{th} can be expressed as voltage between gate and source when low operating current value is $I_D = 100 \mu\text{A}$ for this product. For normal switching operation, $V_{GS(on)}$ requires higher voltage than V_{th} and $V_{GS(off)}$ requires lower voltage than V_{th} . (Relationship can be established as follows: $V_{GS(off)} < V_{th} < V_{GS(on)}$)

Please take this into consideration for using the device. V_{GS} recommended voltage of 1.5 V or higher to turn on this product.

(Q1, Q2 common)



(Q1, Q2 common)



RESTRICTIONS ON PRODUCT USE

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